最终数据手册

英飞凌工业用CoolSiC ™ 1200 V SiC 沟槽MOSFET：采用 .XT 互连技术的碳化硅 MOSFET

特性

- T_{vj} = 25°C时V_{DSS} = 1200 V
- I_{DDC} = 70 A at T_C = 25°C
- $R_{DS(on)}$ = 30 mΩ at V_{GS} = 18 V, T_{vj} = 25°C
- 开关损耗非常低
- 短路耐受时间 3 µs
- 基准栅极阈值电压，$V_{GS(th)}$ = 4.2 V
- 具有抗寄生导通能力，可应用 0 V 关断栅极电压
- 坚固的体二极管，适用于硬换向
- 英飞凌.XT 互连技术，实现、行业领先的热性能

Halogen-free
Green
Lead-free
RoHS

潜在应用

- 通用驱动器 (GPD)
- 电动汽车充电桩
- 在线式UPS/工业UPS
- 组串式逆变器
- 太阳能优化器

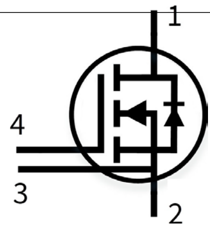
产品验证

- 符合JEDEC47/20/22相关测试的工业应用要求

描述

1 - 漏极
2 - 来源
3 - 开尔文检测
4 – 栅极

注：源极和开尔文传感触点引脚不可互换，互换可能会导致故障（仅适用于 4 pin及TO263-7L封装）



Type	Package	Marking
IMZA120R030M1H	PG-TO247-4-U02	12M1H030

本数据手册的原文使用英文撰写。为方便起见，英飞凌提供了译文；由于翻译过程中可能使用了自动化工具，英飞凌不保证译文的准确性。 为确认准确性，请务必访问 infineon.com 参考最新的英文版本（控制文档）。

目录

1 封装

表1 特征值

Parameter	Symbol	Note or test condition	Values			Unit
			Min.	Typ.	Max.	
Storage temperature	T_{stg}		-55		150	°C
Soldering temperature	T_{sold}	wave soldering 1.6 mm (0.063 in.) from case for 10 s			260	°C
Mounting torque	M	M3 screw, Maximum of mounting processes: 3			0.6	Nm
Thermal resistance, junction-ambient	$R_{th(j-a)}$				62	K/W
MOSFET/body diode thermal resistance, junction-case	$R_{th(j-c)}$			0.42	0.55	K/W

2 MOSFET

表2 最大额定值

Parameter	Symbol	Note or test condition		Values	Unit
Drain-source voltage	V_{DSS}	$T_{vj} \geq 25$ °C		1200	V
Continuous DC drain current for $R_{th(j-c,max)}$, limited by $T_{vj(max)}$	I_{DDC}	$V_{GS} = 18$ V	$T_c = 25$ °C	70	A
			$T_c = 100$ °C	49	
Peak drain current, t_p limited by $T_{vj(max)}$	I_{DM}	$V_{GS} = 18$ V		147	A
Gate-source voltage, max. transient voltage[1)]	V_{GS}	$t_p \leq 0.5$ µs, $D < 0.01$		-10/23	V
Gate-source voltage, max. static voltage	V_{GS}			-7/20	V
Avalanche energy, single pulse	E_{AS}	$I_D = 25$ A, $V_{DD} = 50$ V, $L = 1.4$ mH		450	mJ
Avalanche energy, repetitive	E_{AR}	$I_D = 25$ A, $V_{DD} = 50$ V, $L = 7.1$ µH		2.23	mJ
Short-circuit withstand time	t_{SC}	$V_{DD} \leq 800$ V, $V_{DS,peak} < 1200$ V, $V_{GS(on)} = 15$ V, $T_{vj(start)} = 25$ °C		3	µs
Power dissipation, limited by $T_{vj(max)}$	P_{tot}		$T_c = 25$ °C	273	W
			$T_c = 100$ °C	136	

1) 重要提示：正、负栅极源电压的选择会影响器件的长期行为。必须考虑应用说明 AN2018-09 中描述的设计指南，以确保设备在计划的使用寿命内正常运行。

表 3 建议值

Parameter	Symbol	Note or test condition	Values	Unit
Recommended turn-on gate voltage	$V_{GS(on)}$		15...18	V
Recommended turn-off gate voltage	$V_{GS(off)}$		-5...0	V

表4 特征值

Parameter	Symbol	Note or test condition		Min.	Typ.	Max.	Unit
Drain-source on-state resistance	$R_{DS(on)}$	I_D = 25.6 A	T_{vj} = 25 °C, $V_{GS(on)}$ = 18 V		30	40.9	mΩ
			T_{vj} = 100 °C, $V_{GS(on)}$ = 18 V		41		
			T_{vj} = 175 °C, $V_{GS(on)}$ = 18 V		50		
			T_{vj} = 25 °C, $V_{GS(on)}$ = 15 V		38	56	
Gate-source threshold voltage	$V_{GS(th)}$	I_D = 11 mA, V_{DS} = V_{GS} (tested after 1 ms pulse at V_{GS} = 20 V)	T_{vj} = 25 °C	3.5	4.2	5.2	V
			T_{vj} = 175 °C		3.6		
Zero gate-voltage drain current	I_{DSS}	V_{DS} = 1200 V, V_{GS} = 0 V	T_{vj} = 25 °C			200	µA
			T_{vj} = 175 °C		3.4		
Gate leakage current	I_{GSS}	V_{DS} = 0 V	V_{GS} = 23 V			100	nA
			V_{GS} = -10 V			-100	
Forward transconductance	g_{fs}	I_D = 25.6 A, V_{DS} = 20 V			13		S
Internal gate resistance	$R_{G,int}$	f = 1 MHz, V_{AC} = 25 mV			2.1		Ω
Input capacitance	C_{iss}	V_{DS} = 800 V, V_{GS} = 0 V, f = 100 kHz, V_{AC} = 25 mV			2160		pF
Output capacitance	C_{oss}	V_{DS} = 800 V, V_{GS} = 0 V, f = 100 kHz, V_{AC} = 25 mV			99		pF
Reverse transfer capacitance	C_{rss}	V_{DS} = 800 V, V_{GS} = 0 V, f = 100 kHz, V_{AC} = 25 mV			14		pF
C_{oss} stored energy	E_{oss}	V_{DS} = 800 V, V_{GS} = 0 V, f = 100 kHz, V_{AC} = 25 mV			40		µJ
Total gate charge	Q_G	V_{DD} = 800 V, I_D = 25.6 A, V_{GS} = -2/18 V, turn-on pulse			68		nC
Plateau gate charge	$Q_{GS(pl)}$	V_{DD} = 800 V, I_D = 25.6 A, V_{GS} = -2/18 V, turn-on pulse			16.9		nC
Gate-to-drain charge	Q_{GD}	V_{DD} = 800 V, I_D = 25.6 A, V_{GS} = -2/18 V, turn-on pulse			13.6		nC

（表格续下页......）

表 4 （续） 特征值

Parameter	Symbol	Note or test condition		Values Min.	Typ.	Max.	Unit
Turn-on delay time	$t_{d(on)}$	V_{DD} = 800 V, I_D = 25.6 A, V_{GS} = 0/18 V, $R_{GS(on)}$ = 1 Ω, $R_{GS(off)}$ = 1 Ω, L_σ = 15 nH, diode: body diode at V_{GS} = 0 V	T_{vj} = 25 °C		23		ns
			T_{vj} = 175 °C		22		
Rise time	t_r	V_{DD} = 800 V, I_D = 25.6 A, V_{GS} = 0/18 V, $R_{GS(on)}$ = 1 Ω, $R_{GS(off)}$ = 1 Ω, L_σ = 15 nH, diode: body diode at V_{GS} = 0 V	T_{vj} = 25 °C		8.5		ns
			T_{vj} = 175 °C		9.7		
Turn-off delay time	$t_{d(off)}$	V_{DD} = 800 V, I_D = 25.6 A, V_{GS} = 0/18 V, $R_{GS(on)}$ = 1 Ω, $R_{GS(off)}$ = 1 Ω, L_σ = 15 nH, diode: body diode at V_{GS} = 0 V	T_{vj} = 25 °C		27.3		ns
			T_{vj} = 175 °C		28		
Fall time	t_f	V_{DD} = 800 V, I_D = 25.6 A, V_{GS} = 0/18 V, $R_{GS(on)}$ = 1 Ω, $R_{GS(off)}$ = 1 Ω, L_σ = 15 nH, diode: body diode at V_{GS} = 0 V	T_{vj} = 25 °C		9.2		ns
			T_{vj} = 175 °C		9.2		
Turn-on energy	E_{on}	V_{DD} = 800 V, I_D = 25.6 A, V_{GS} = 0/18 V, $R_{GS(on)}$ = 1 Ω, $R_{GS(off)}$ = 1 Ω, L_σ = 15 nH, diode: body diode at V_{GS} = 0 V	T_{vj} = 25 °C		230		µJ
			T_{vj} = 175 °C		392		
Turn-off energy	E_{off}	V_{DD} = 800 V, I_D = 25.6 A, V_{GS} = 0/18 V, $R_{GS(on)}$ = 1 Ω, $R_{GS(off)}$ = 1 Ω, L_σ = 15 nH, diode: body diode at V_{GS} = 0 V	T_{vj} = 25 °C		60		µJ
			T_{vj} = 175 °C		65		
Total switching energy	E_{tot}	V_{DD} = 800 V, I_D = 25.6 A, V_{GS} = 0/18 V, $R_{GS(on)}$ = 1 Ω, $R_{GS(off)}$ = 1 Ω, L_σ = 15 nH, diode: body diode at V_{GS} = 0 V	T_{vj} = 25 °C		330		µJ
			T_{vj} = 175 °C		618		

（表格续下页……）

表 4（续） 特征值

Parameter	Symbol	Note or test condition	Values			Unit
			Min.	Typ.	Max.	
Virtual junction temperature	T_{vj}		-55		175	°C

注意：为了获得最佳的使用寿命和可靠性，英飞凌建议工作条件不超过本数据手册中所述最大额定值的 80%。

该芯片技术的特征高达200 kV/μs。测量的dV/dt 受到测量测试设置和封装的限制。

动态测试电路见图F。

3 体二极管（MOSFET）

表5 最大额定值

Parameter	Symbol	Note or test condition		Values	Unit
Drain-source voltage	V_{DSS}	$T_{vj} \geq 25$ °C		1200	V
Continuous reverse drain current for $R_{th(j-c,max)}$, limited by $T_{vj(max)}$	I_{SDC}	$V_{GS} = 0$ V	$T_c = 25$ °C	66	A
			$T_c = 100$ °C	41	
Peak reverse drain current, t_p limited by $T_{vj(max)}$	I_{SM}	$V_{GS} = 0$ V		147	A

表6 特征值

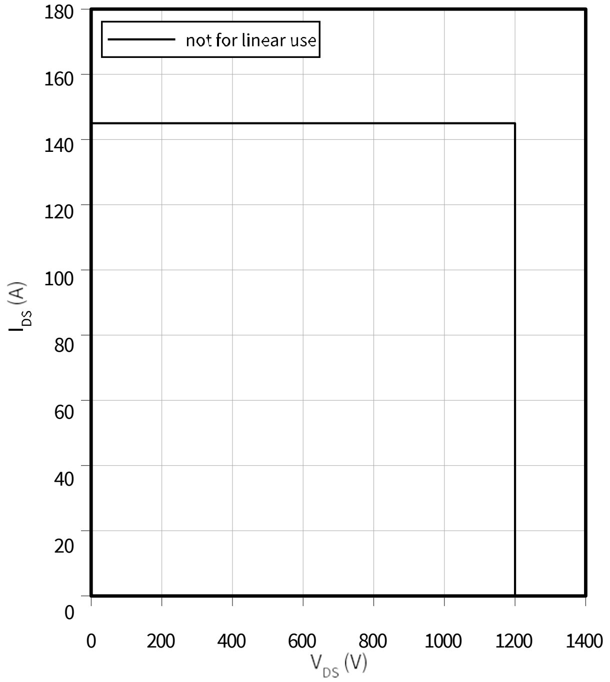
Parameter	Symbol	Note or test condition		Values			Unit
				Min.	Typ.	Max.	
Drain-source reverse voltage	V_{SD}	$I_{SD} = 25.6$ A, $V_{GS} = 0$ V	$T_{vj} = 25$ °C		3.8	5	V
			$T_{vj} = 100$ °C		3.7		
			$T_{vj} = 175$ °C		3.6		
MOSFET forward recovery charge	Q_{fr}	$V_{DD} = 800$ V, $I_{SD} = 25.6$ A, $V_{GS} = 0$ V, $-di_{SD}/dt = 3000$ A/μs, Q_{fr} includes also Q_C	$T_{vj} = 25$ °C		210		nC
			$T_{vj} = 175$ °C		388		
MOSFET peak forward recovery current	I_{frm}	$V_{DD} = 800$ V, $I_{SD} = 25.6$ A, $V_{GS} = 0$ V, $-di_{SD}/dt = 3000$ A/μs, Q_{fr} includes also Q_C	$T_{vj} = 25$ °C		23		A
			$T_{vj} = 175$ °C		37		
MOSFET forward recovery energy	E_{fr}	$V_{DD} = 800$ V, $I_{SD} = 25.6$ A, $V_{GS} = 0$ V, $-di_{SD}/dt = 3000$ A/μs, Q_{fr} includes also Q_C	$T_{vj} = 25$ °C		40		μJ
			$T_{vj} = 175$ °C		161		
Virtual junction temperature	T_{vj}			-55		175	°C

4 特性图

Reverse bias safe operating area (RBSOA)

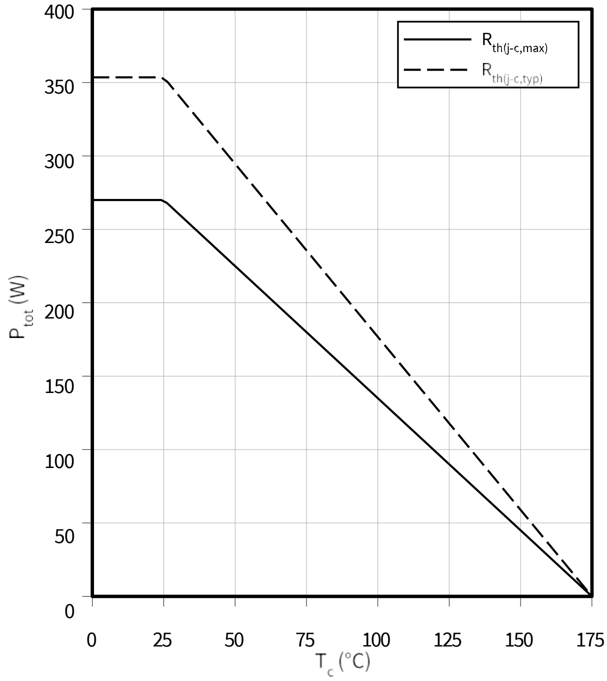
$I_{DS} = f(V_{DS})$

$T_{vj} \leq 175$ °C, $V_{GS} = 0/18$ V, $T_c = 25$ °C



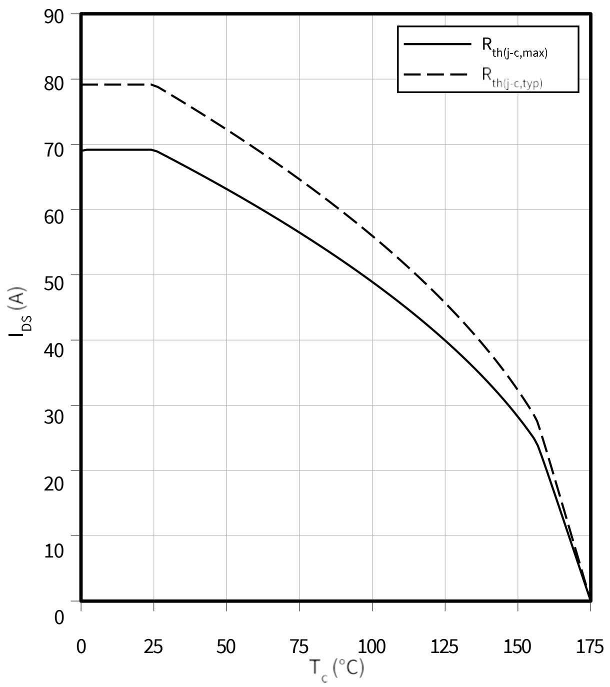
Power dissipation as a function of case temperature limited by bond wire

$P_{tot} = f(T_c)$



Maximum DC drain to source current as a function of case temperature limited by bond wire

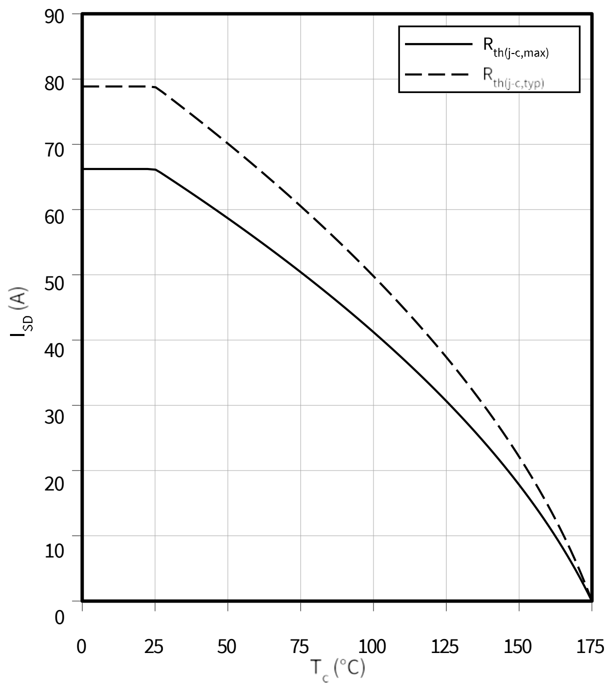
$I_{DS} = f(T_c)$



Maximum source to drain current as a function of case temperature limited by bond wire

$I_{SD} = f(T_c)$

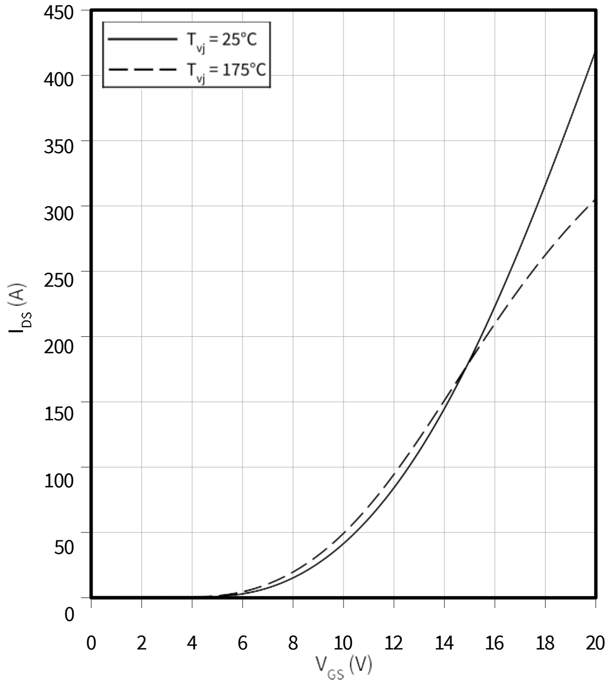
$V_{GS} = 0$ V



Typical transfer characteristic

$I_{DS} = f(V_{GS})$

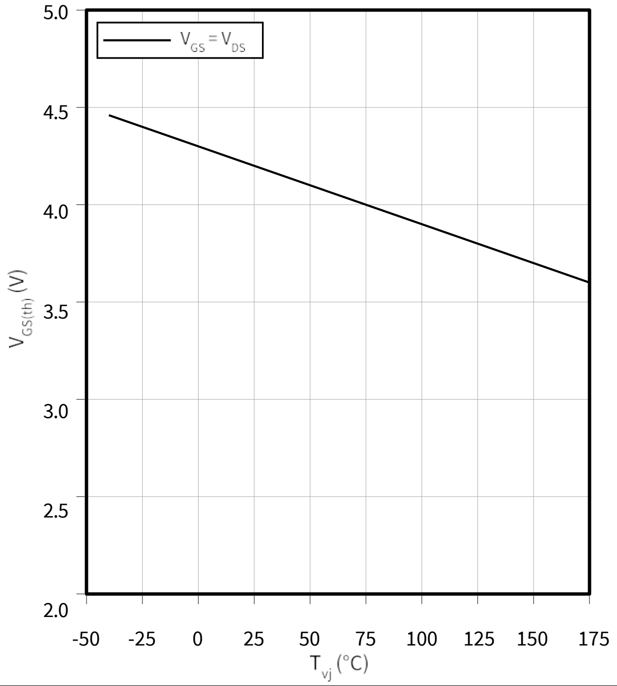
$V_{DS} = 20$ V, $t_p = 20$ µs



Typical gate-source threshold voltage as a function of junction temperature

$V_{GS(th)} = f(T_{vj})$

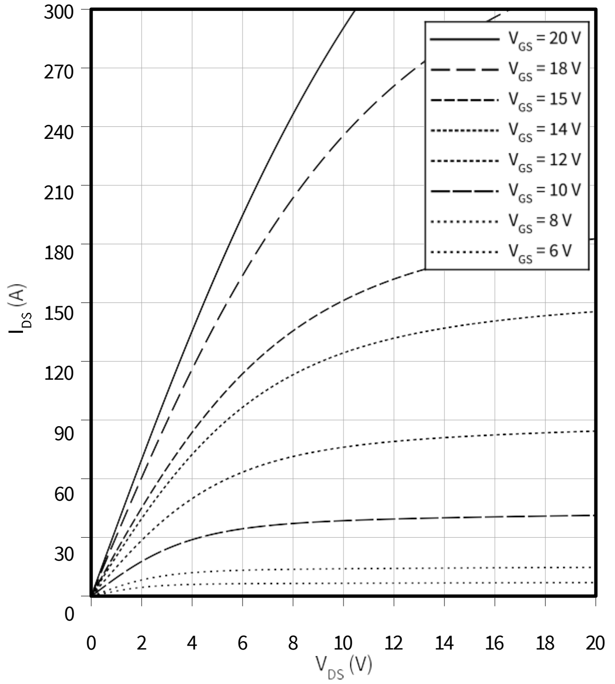
$I_D = 11$ mA



Typical output characteristic, V_{GS} as parameter

$I_{DS} = f(V_{DS})$

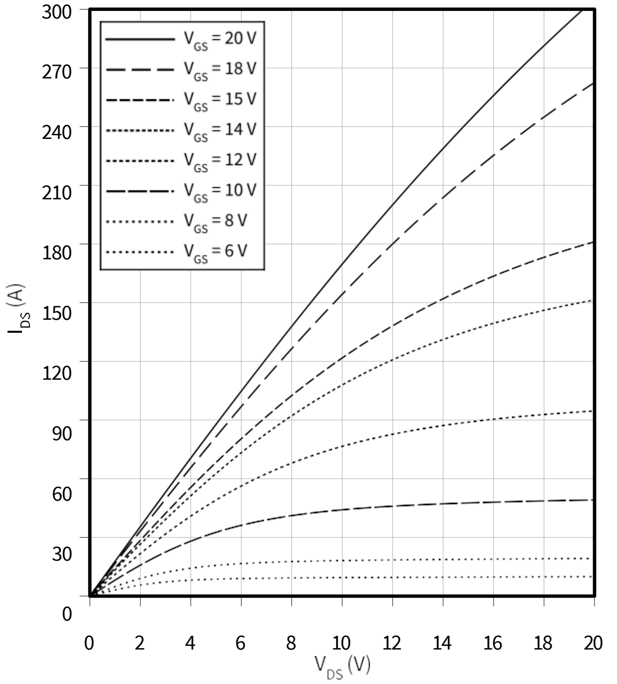
$T_{vj} = 25$ °C, $t_p = 20$ µs



Typical output characteristic, V_{GS} as parameter

$I_{DS} = f(V_{DS})$

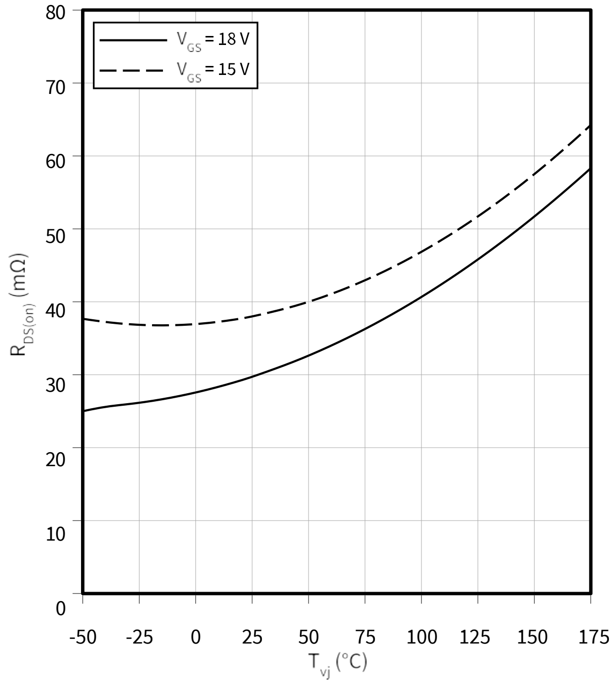
$T_{vj} = 175$ °C, $t_p = 20$ µs



Typical on-state resistance as a function of junction temperature

$R_{DS(on)} = f(T_{vj})$

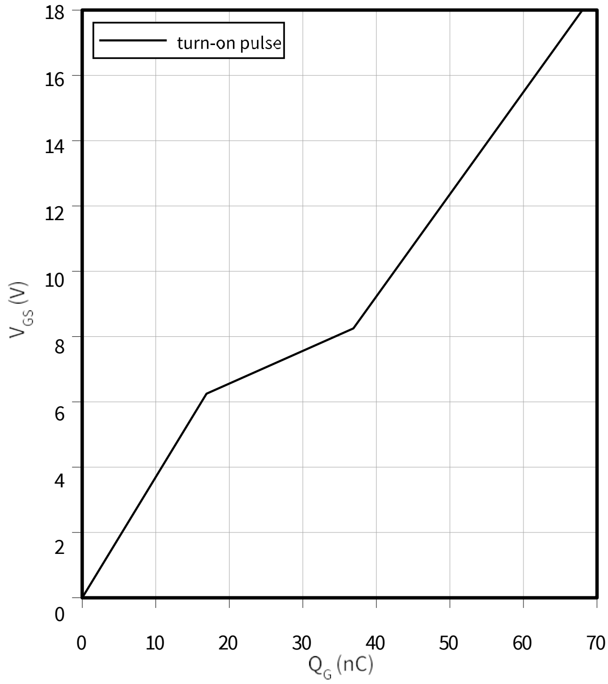
$I_D = 25.6$ A



Typical gate charge

$V_{GS} = f(Q_G)$

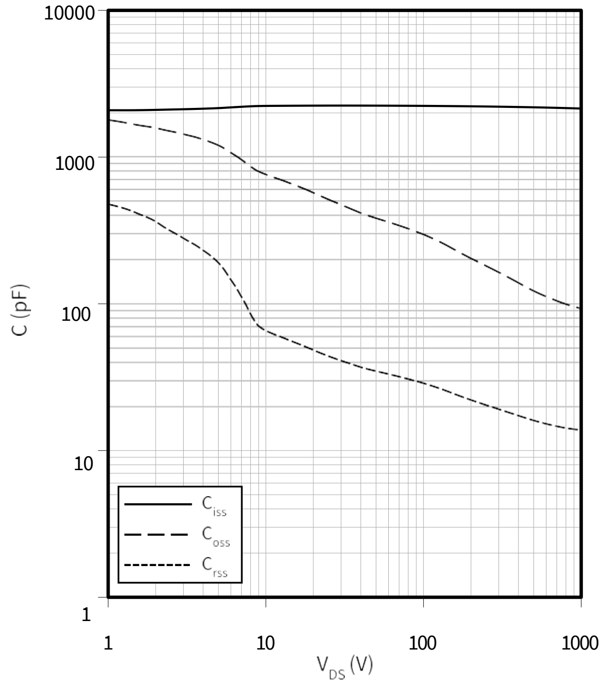
$I_D = 25.6$ A, $V_{DS} = 800$ V



Typical capacitance as a function of drain-source voltage

$C = f(V_{DS})$

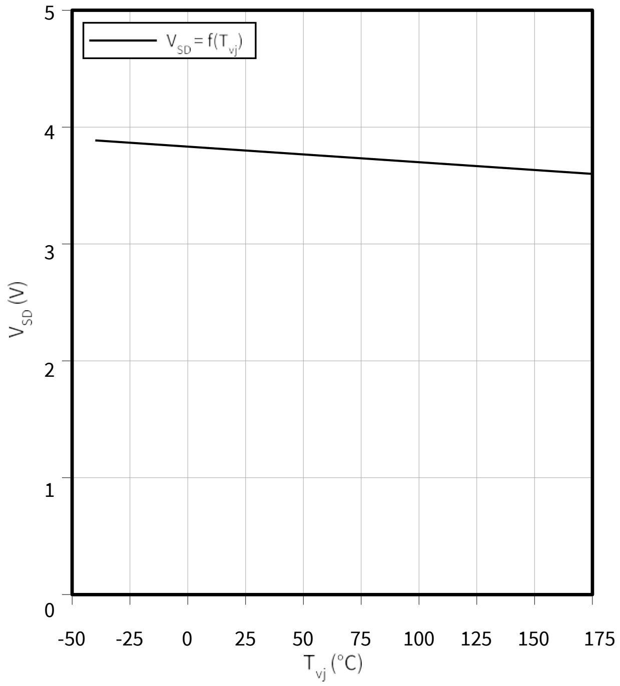
$f = 100$ kHz, $V_{GS} = 0$ V



Typical reverse drain voltage as function of junction temperature

$V_{SD} = f(T_{vj})$

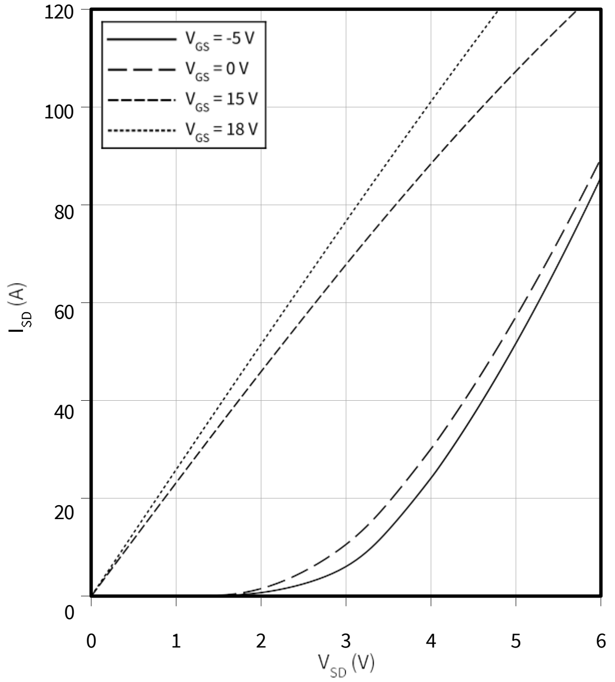
$I_{SD} = 25$ A, $V_{GS} = 0$ V



Typical reverse drain current as function of reverse drain voltage, V_{GS} as parameter

$I_{SD} = f(V_{SD})$

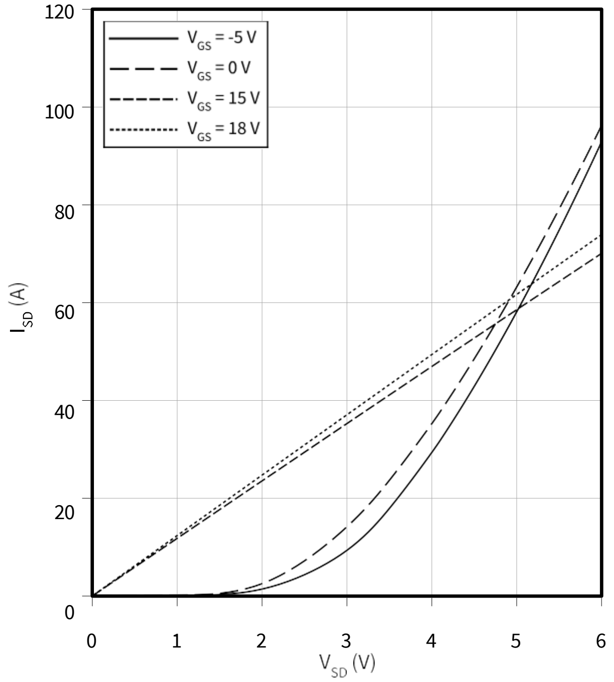
$T_{vj} = 25$ °C, $t_p = 20$ µs



Typical reverse drain current as function of reverse drain voltage, V_{GS} as parameter

$I_{SD} = f(V_{SD})$

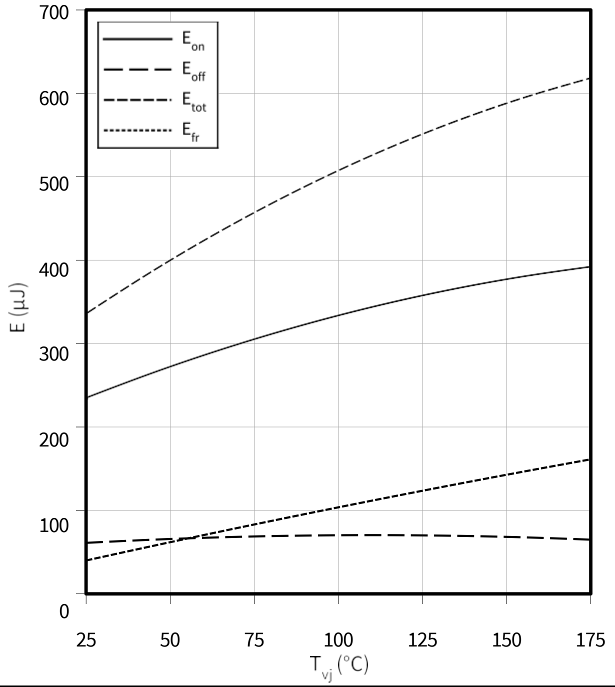
$T_{vj} = 175$ °C, $t_p = 20$ µs



Typical switching energy as a function of junction temperature, test circuit in Fig. F, 2nd device own body diode: $V_{GS} = 0$ V

$E = f(T_{vj})$

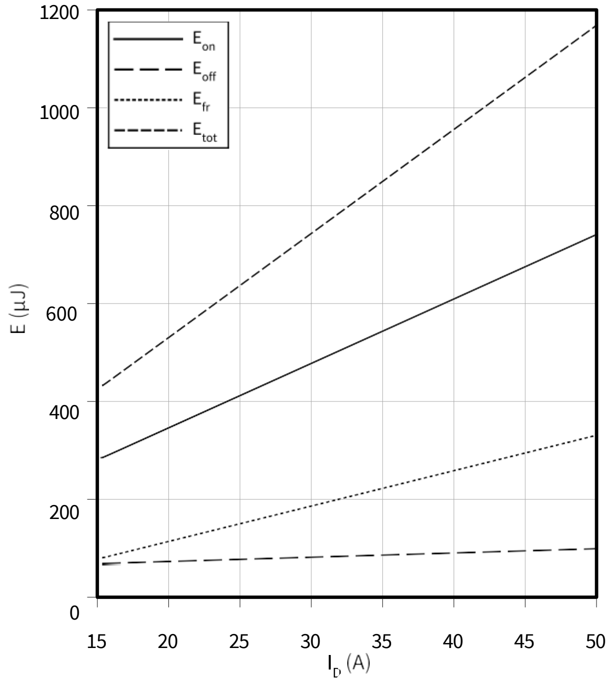
$V_{GS} = 0/18$ V, $I_D = 25.6$ A, $R_{G,ext} = 1$ Ω, $V_{DD} = 800$ V



Typical switching energy as a function of drain current, test circuit in Fig. F, 2nd device own body diode: $V_{GS} = 0$ V

$E = f(I_D)$

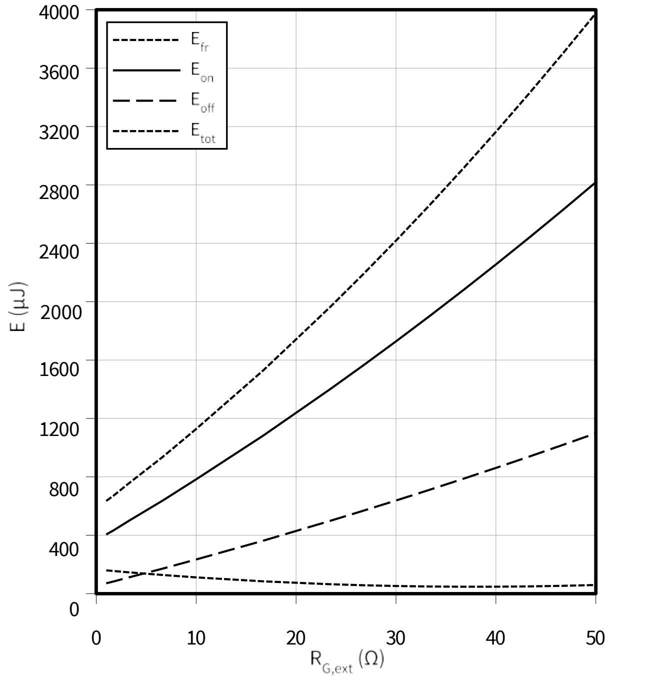
$V_{GS} = 0/18$ V, $T_{vj} = 175$ °C, $R_{G,ext} = 1$ Ω, $V_{DD} = 800$ V



Typical switching energy losses as a function of gate resistance, test circuit in Fig. F, 2nd device own body diode: V_{GS} = 0 V

$E = f(R_{G,ext})$

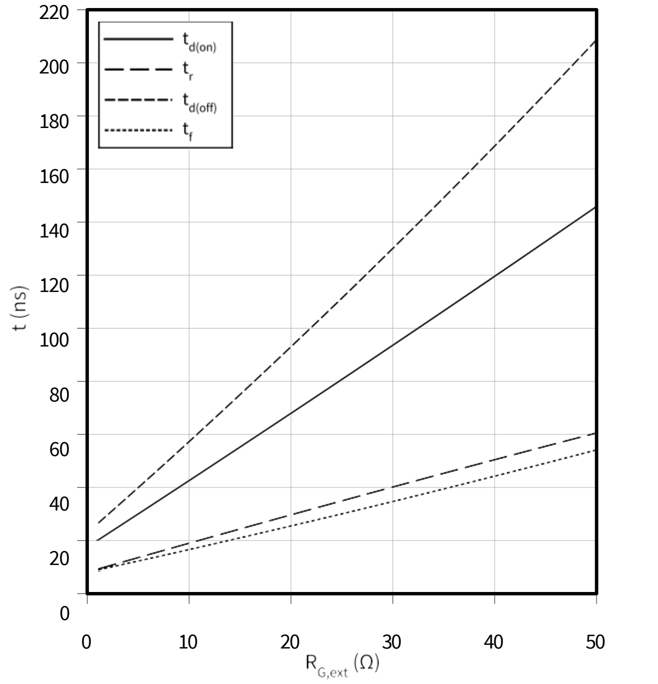
V_{GS} = 0/18 V, I_D = 25.6 A, T_{vj} = 175 °C, V_{DD} = 800 V



Typical switching times as a function of gate resistance, test circuit in Fig. F, 2nd device own body diode: V_{GS} = 0 V

$t = f(R_{G,ext})$

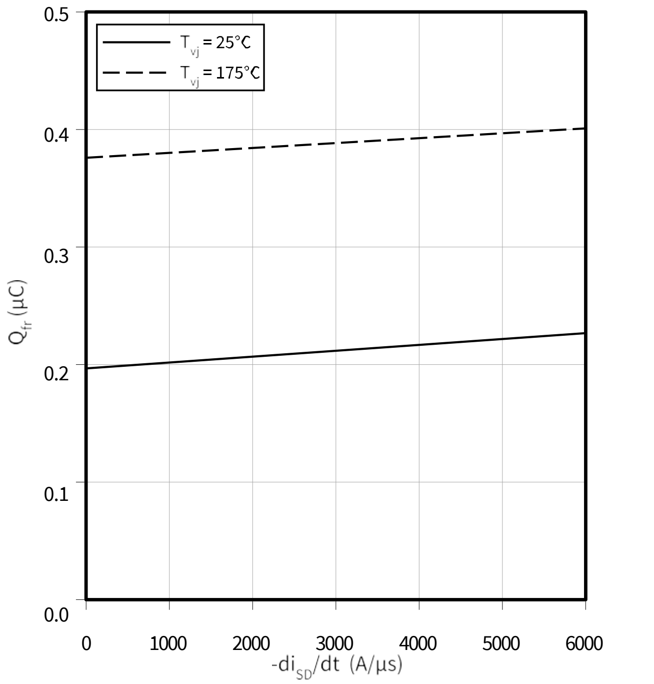
V_{GS} = 0/18 V, I_D = 25.6 A, T_{vj} = 175 °C, V_{DD} = 800 V



Typical reverse recovery charge as a function of revere drain current slope, test circuit in Fig. F, 2nd device own body diode: V_{GS} = 0 V

$Q_{fr} = f(-di_{SD}/dt)$

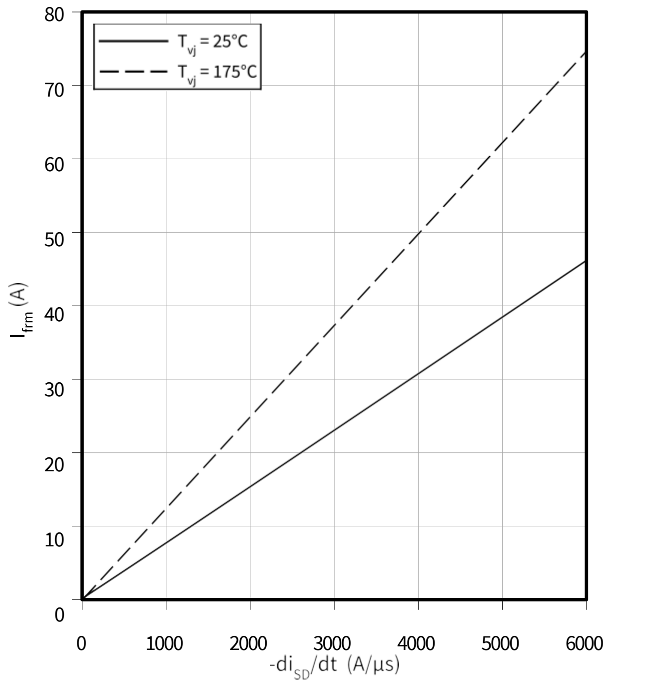
V_{GS} = 0/18 V, I_{SD} = 25.6 A, V_{DD} = 800 V



Typical reverse recovery current as a function of reverse drain current slope, test circuit in Fig. F, 2nd device own body diode: V_{GS} = 0 V

$I_{frm} = f(-di_{SD}/dt)$

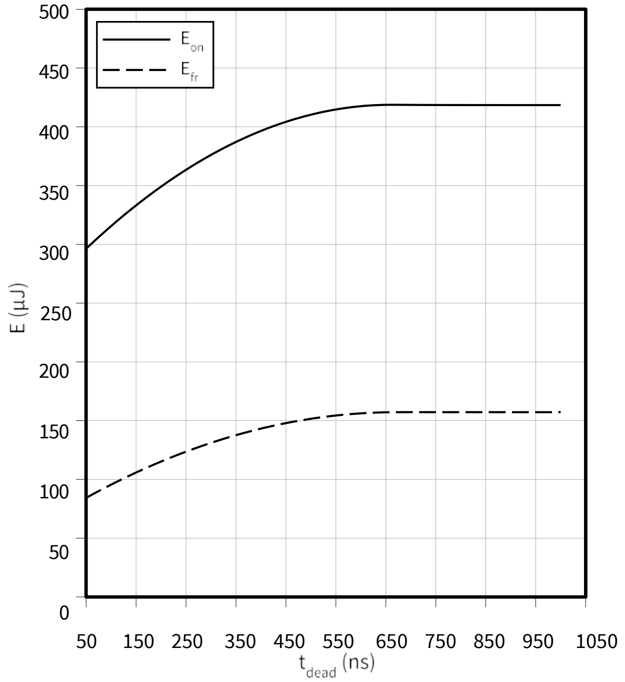
V_{GS} = 0/18 V, I_{SD} = 25.6 A, V_{DD} = 800 V



Typical switching energy losses as a function of dead time / blanking time, test circuit in Fig. F, 2nd device own body diode: V_{GS} = -5 V

$E = f(t_{dead})$

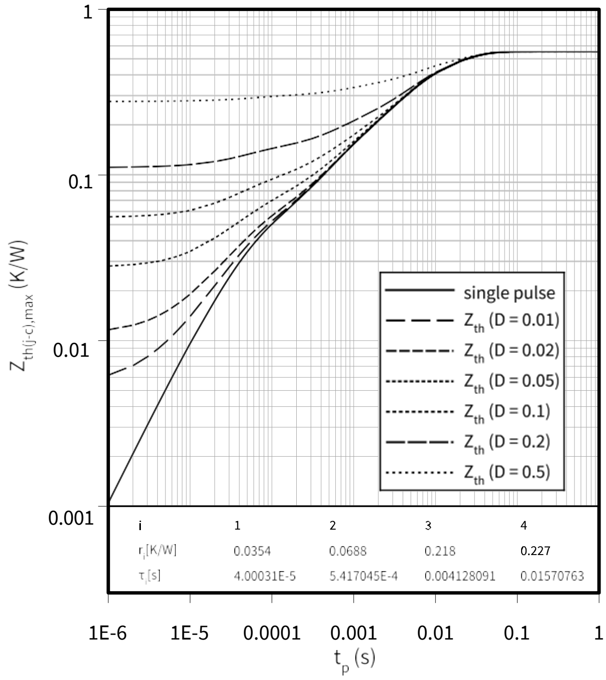
V_{GS} = -5/18 V, I_D = 25.6 A, T_{vj} = 175 °C, V_{DD} = 800 V



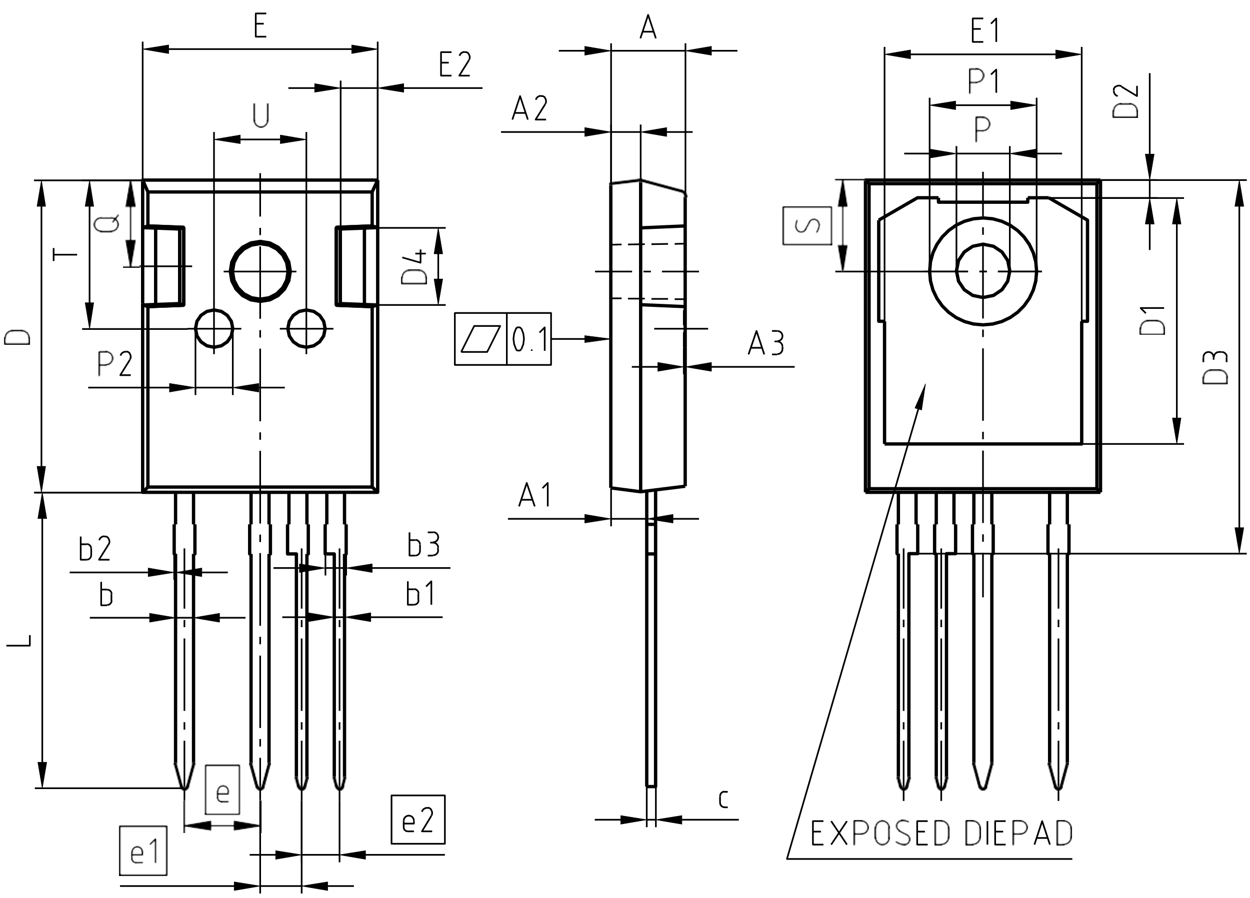
Max. transient thermal impedance (MOSFET/diode)

$Z_{th(j-c),max} = f(t_p)$

$D = t_p/T$



5 封装外形



NOTES:
ALL DIMENSIONS DO NOT INCLUDE MOLD FLASH
OR PROTRUSIONS.

PACKAGE - GROUP NUMBER:	PG-TO247-4-U02				
DIMENSIONS	MILLIMETERS		DIMENSIONS	MILLIMETERS	
	MIN.	MAX.		MIN.	MAX.
A	4.90	5.10	E	15.70	15.90
A1	2.31	2.51	E1	13.10	13.50
A2	1.90	2.10	E2	2.40	2.60
A3	0.05	0.25	e	5.08	
b	1.10	1.30	e1	2.79	
b1	0.65	0.79	e2	2.54	
b2	---	0.20	N	4	
b3	1.34	1.44	L	19.80	20.10
c	0.58	0.66	øP	3.50	3.70
D	20.90	21.10	øP1	7.00	7.40
D1	16.25	16.85	øP2	2.40	2.60
D2	1.05	1.35	Q	5.60	6.00
D3	24.97	25.27	S	6.15	
D4	4.90	5.10	T	9.80	10.20
			U	6.00	6.40

图 1

6 测试条件

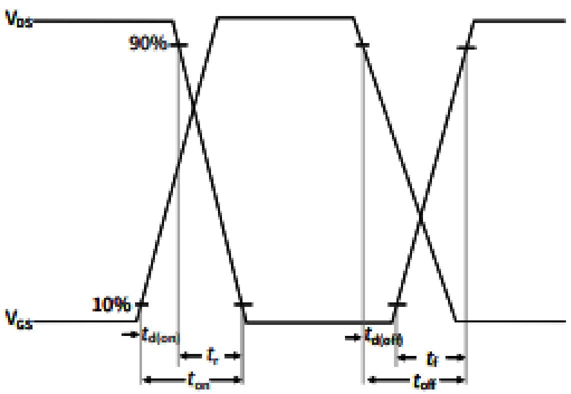


Figure A. **Definition of switching times**

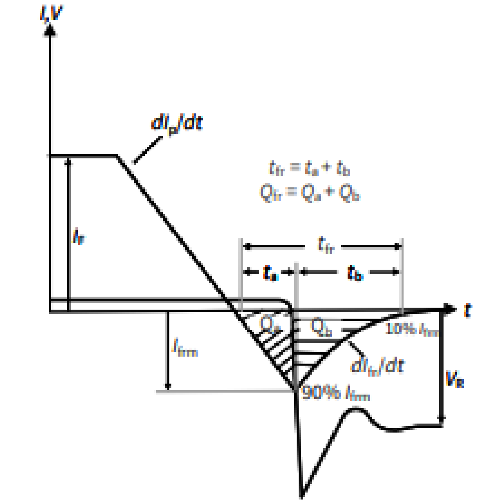


Figure B. **Definition of diode switching characteristics**

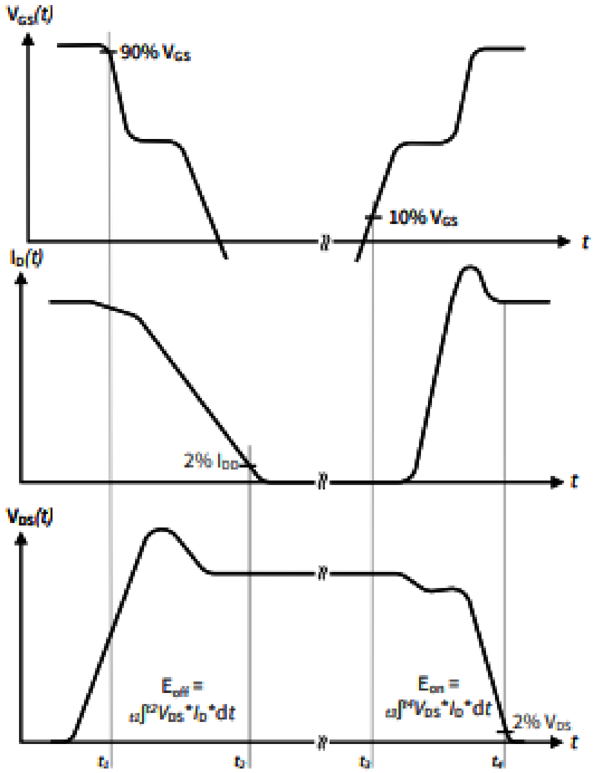


Figure C. **Definition of switching losses**

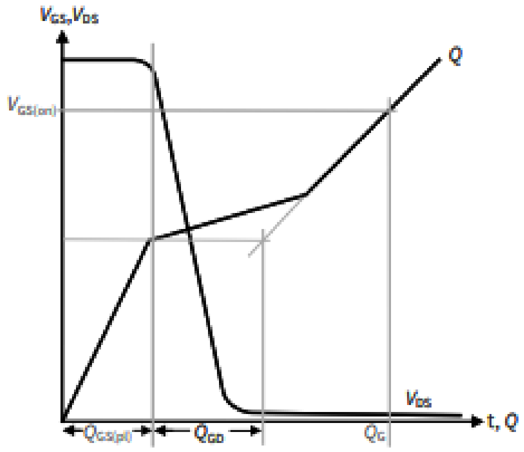


Figure D. **Definition of QGD**

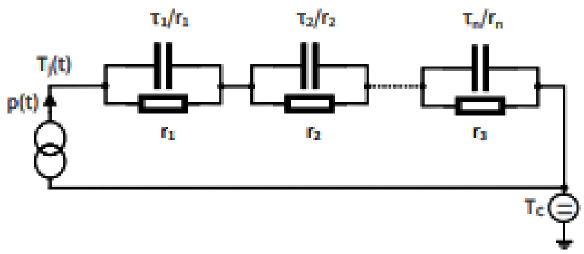


Figure E. **Thermal equivalent circuit**

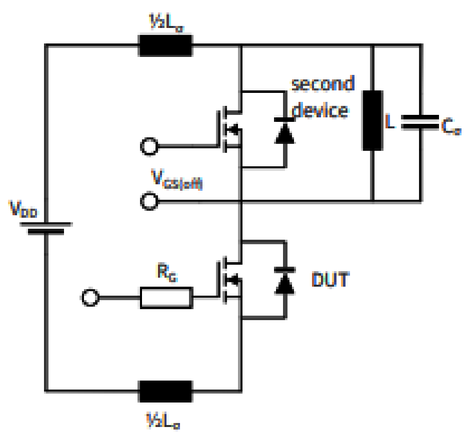


Figure F. **Dynamic test circuit**
Parasitic inductance L_σ,
Parasitic capacitor C_σ,

,

修订记录

Document revision	Date of release	Description of changes
1.00	2022-02-03	Final datasheet
1.10	2022-08-10	Change of test condition of dynamic capacitances in Table 4, “Characteristic values” (C_{iss}, C_{oss}, C_{rss}): V_{DD}= 25 V to V_{DD}= 800 V Correction of unit of “Input capacitance” C_{iss} from nF to pF Change of V_{GS} “Gate-source voltage, max. static voltage” in Table 2, “Maximum rated values” from -5/20 V to -7/20 V Editorial changes in “Features” on page 1 Editorial changes in “Package” on page 1 Correction of unit of x-axis at diagram “Max. transient thermal impedance (MOSFET/diode)” from µs to s, on page 13 Correction of diagram “Max. transient thermal impedance (MOSFET/ diode)”, on page 13
1.20	2023-05-08	Correction of gate charge values in Table 4 Editorial changes
1.30	2024-11-15	Updated package name Corrected forward transconductance g_{fs} in Table 4 Corrected diagram “Typical output characteristic, V_{GS} as parameter" Corrected diagram “Typical transfer characteristic” Editorial changes

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